

### Performance Characteristics

- Frequency range: DC~67GHz
- Attenuation range:  
0/0.5/1/2/3/4/5/6/7/8/9/10/11/15/20/25/30/40dB
- Input/output standing wave: 1.6/1.6
- Chip size: 0.5mmx0.5mmx0.1mm

### Product Introduction

The frequency range covers DC~67GHz, with attenuation values of 0/0.5/1/2/3/4/5/6/7/8/9/10/11/15/20/25/30/40dB.

### Electrical Parameters(TA=+25°C)

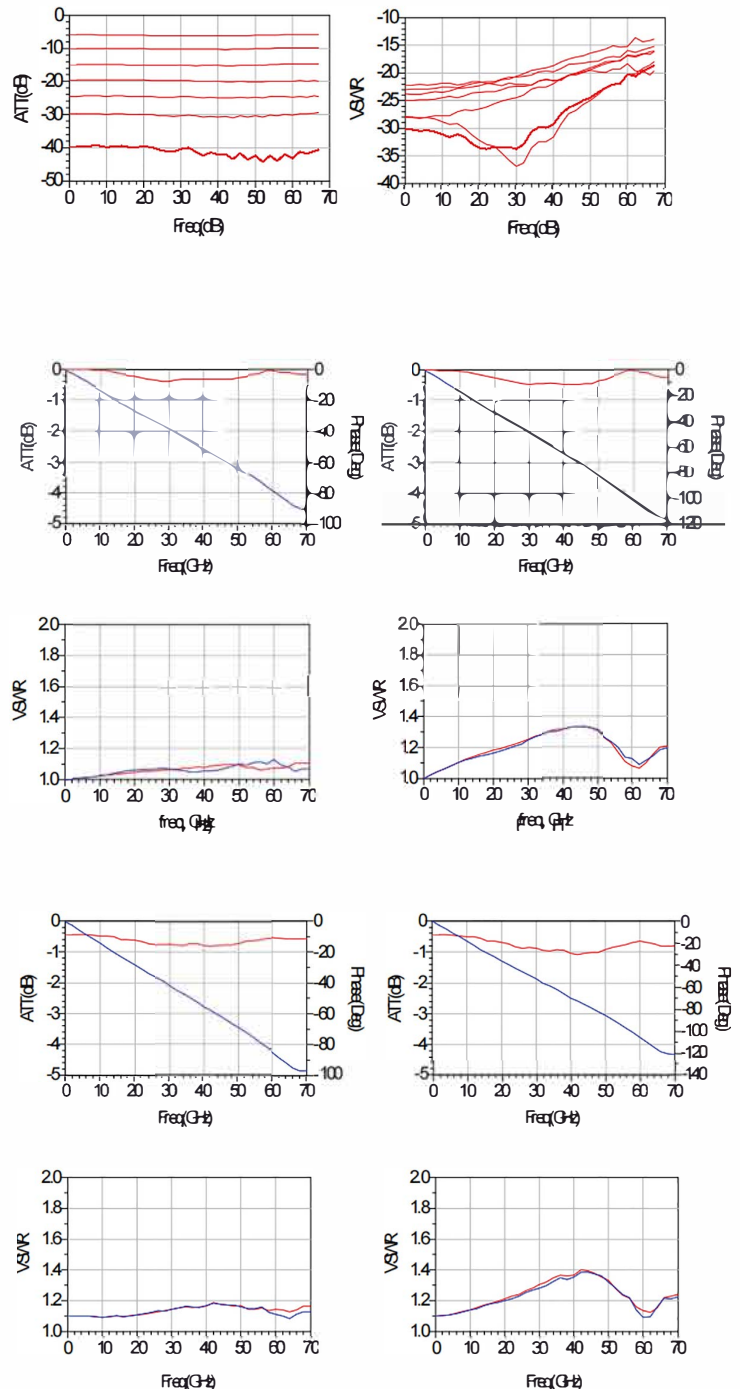
Index	Min	Typ	Max	Unit	
Frequency Range	DC~67			GHz	
Attenuation accuracy	(A)0dB	0	0	0.8	dB
	(B)0.5dB	0.3	0.5	1	dB
	(C)1dB	0.8	1	1.8	dB
	(D)2dB	1.8	2	2.8	dB
	(E)3dB	2.8	3	3.8	dB
	(F)4dB	3.8	4	4.8	dB
	(G)5dB	4.8	5	5.8	dB
	(H)6dB	5.5	6	6.8	dB
	(K) 7dB	6.5	7	7.8	dB
	(L) 8dB	7	8	8.8	dB
	(M) 9dB	8	9	9.8	dB
	(N) 10dB	9	10	10.8	dB
	(P)11dB	10	11	11.8	dB
	(Q)15dB	14.5	15	16	dB
	(S)20dB	19.5	20	21	dB
	(T)0/1/2/3dB		0/1/2/3		dB
(W)5/6/7/8dB		5/6/7/8		dB	
(X)30dB	29	30	31.5	dB	
(Y)40dB	38	40	45	dB	
(TF)25dB	24	25	25.5	dB	
Input standing wave(Bondwire)		1.2	1.6	-	
Output standing wave(Bondwire)		1.2	1.6	-	
Input standing wave(On-wafer)		1.2	1.5	-	
Output standing wave(On-wafer)		1.2	1.5	-	

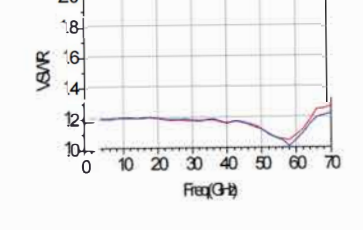
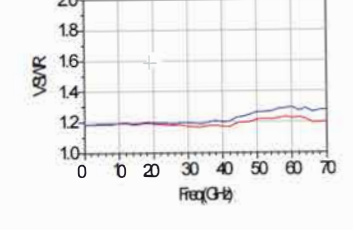
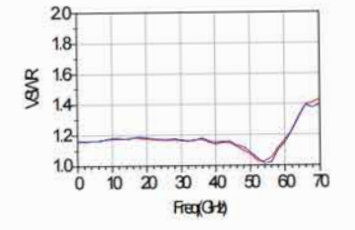
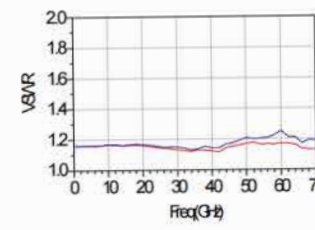
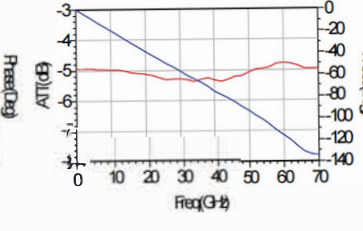
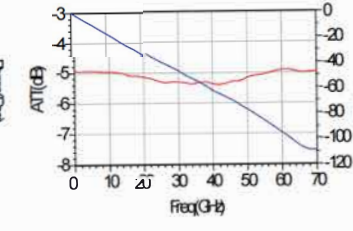
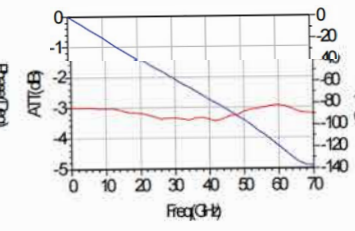
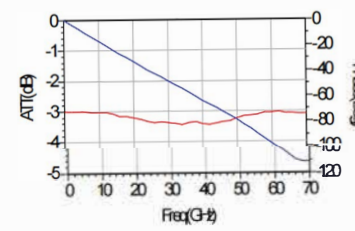
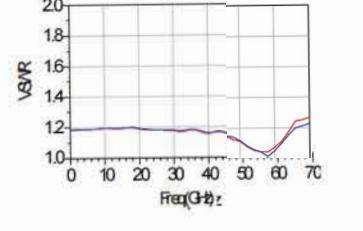
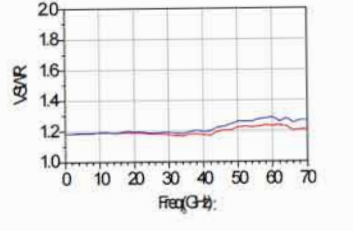
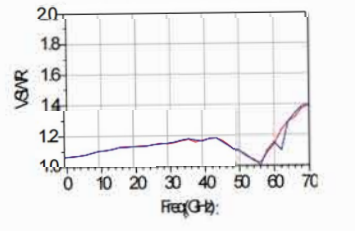
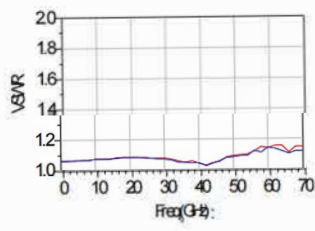
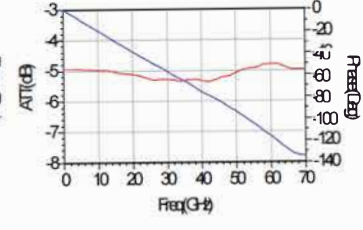
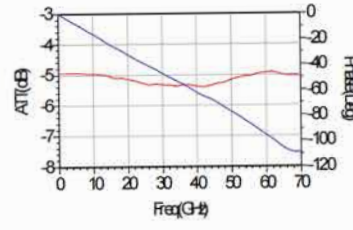
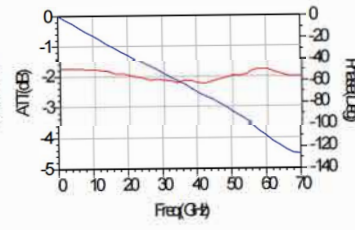
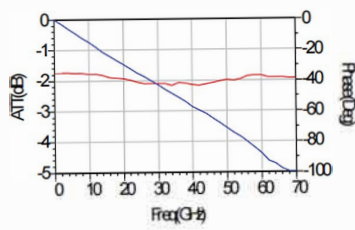
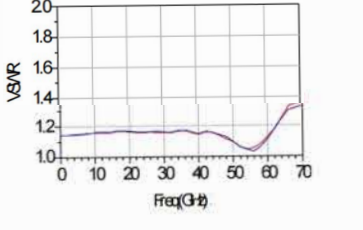
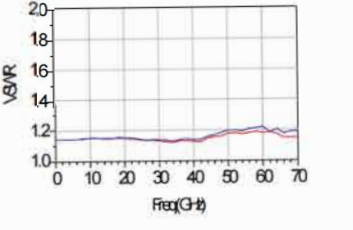
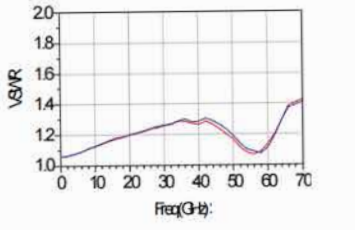
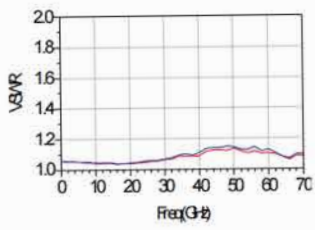
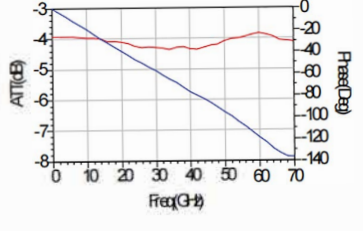
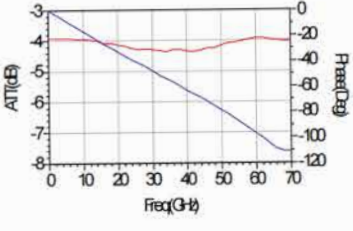
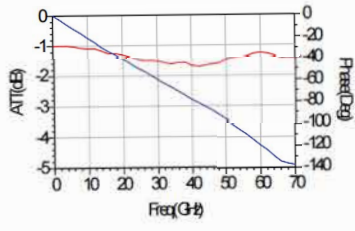
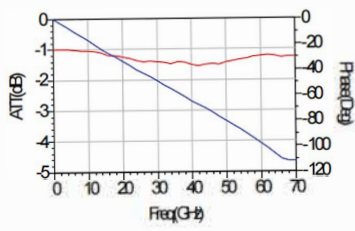
### Use Restriction Parameters

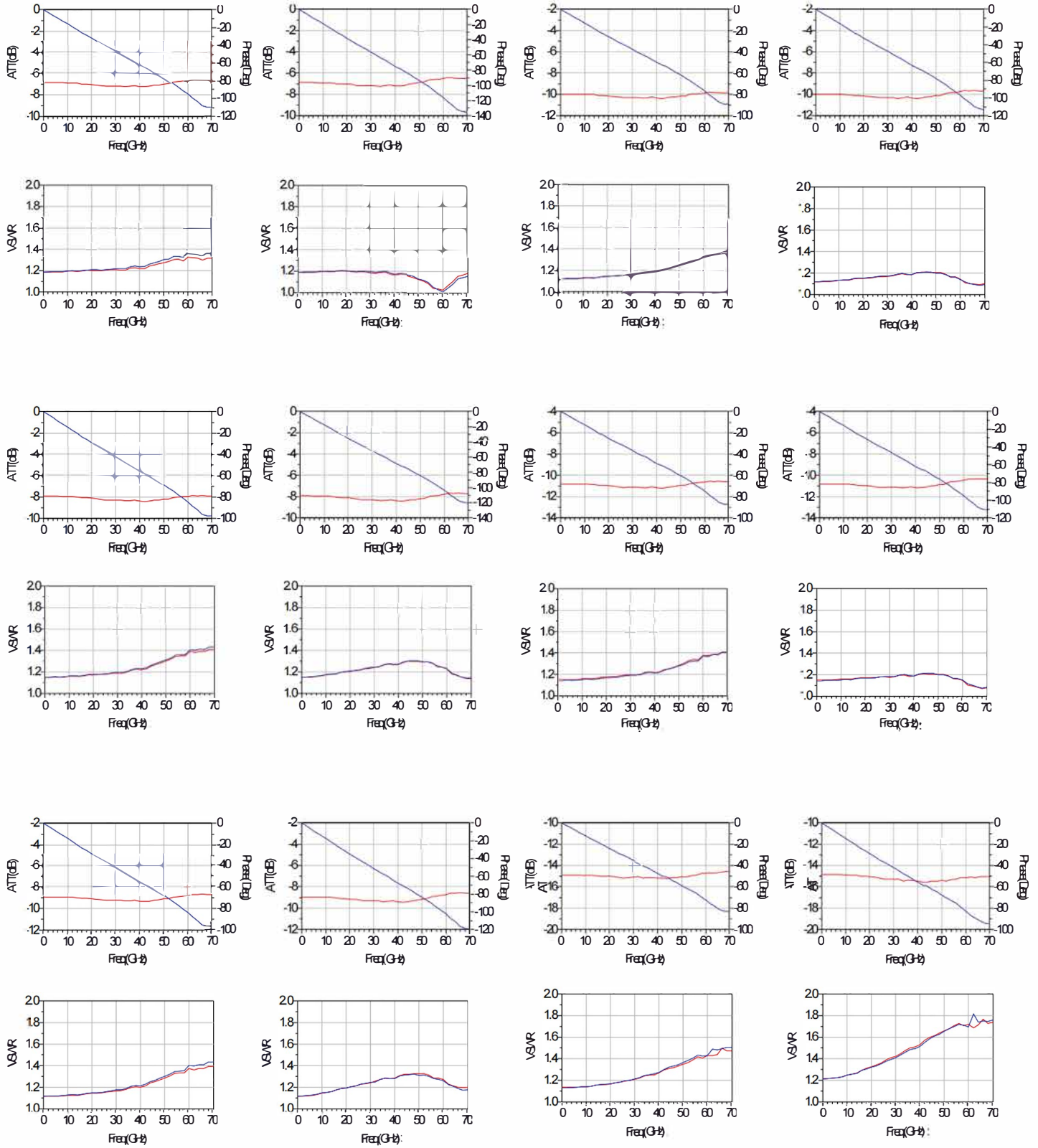
Maximum Input Power	+20dBm
Storage Temperature	-65°C ~ +150°C
Operating Temperature	-55°C ~ +125°C

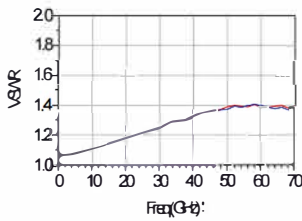
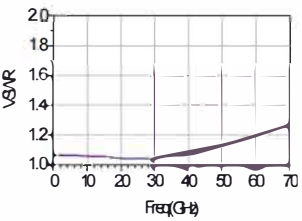
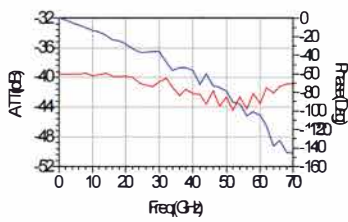
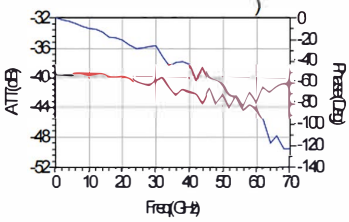
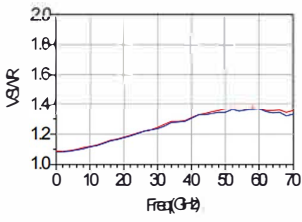
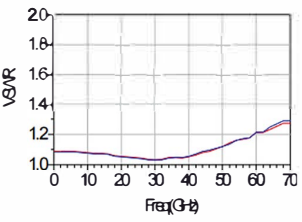
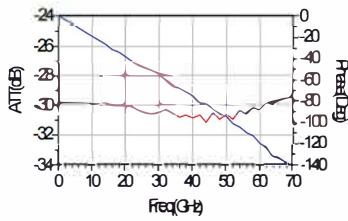
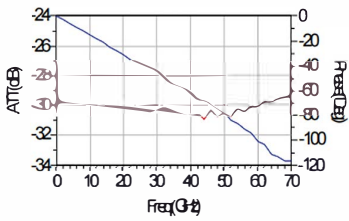
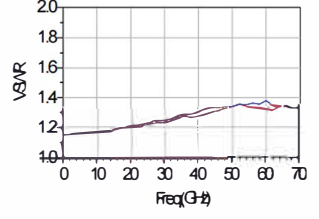
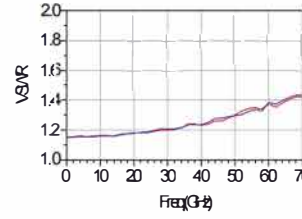
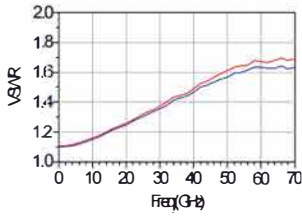
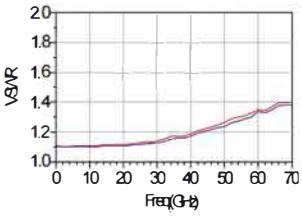
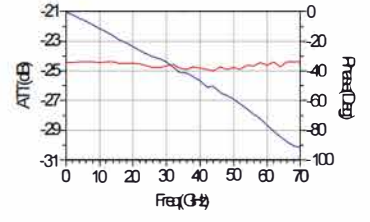
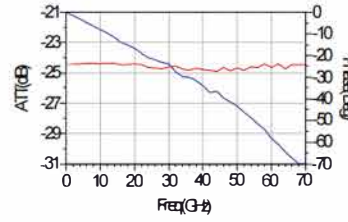
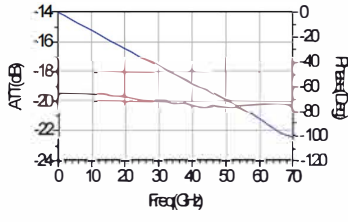
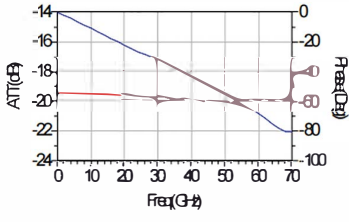
### Typical Curve

In order to provide users with a more intuitive understanding of the performance indicators of the chip, the following are curve graphs for each indicator.

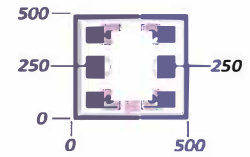
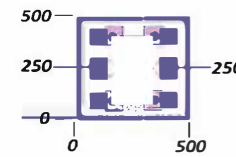
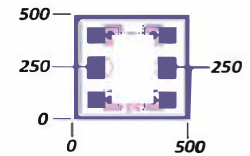
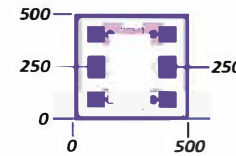
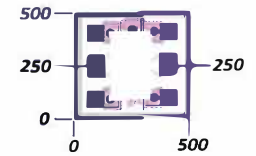
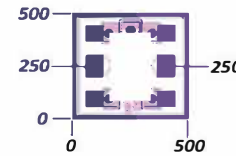
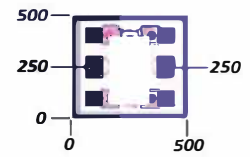
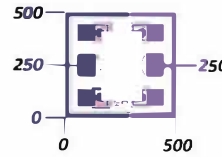






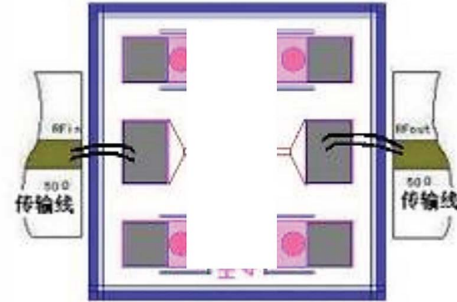


**External Dimensions**



**Suggested Assembly Diagram**

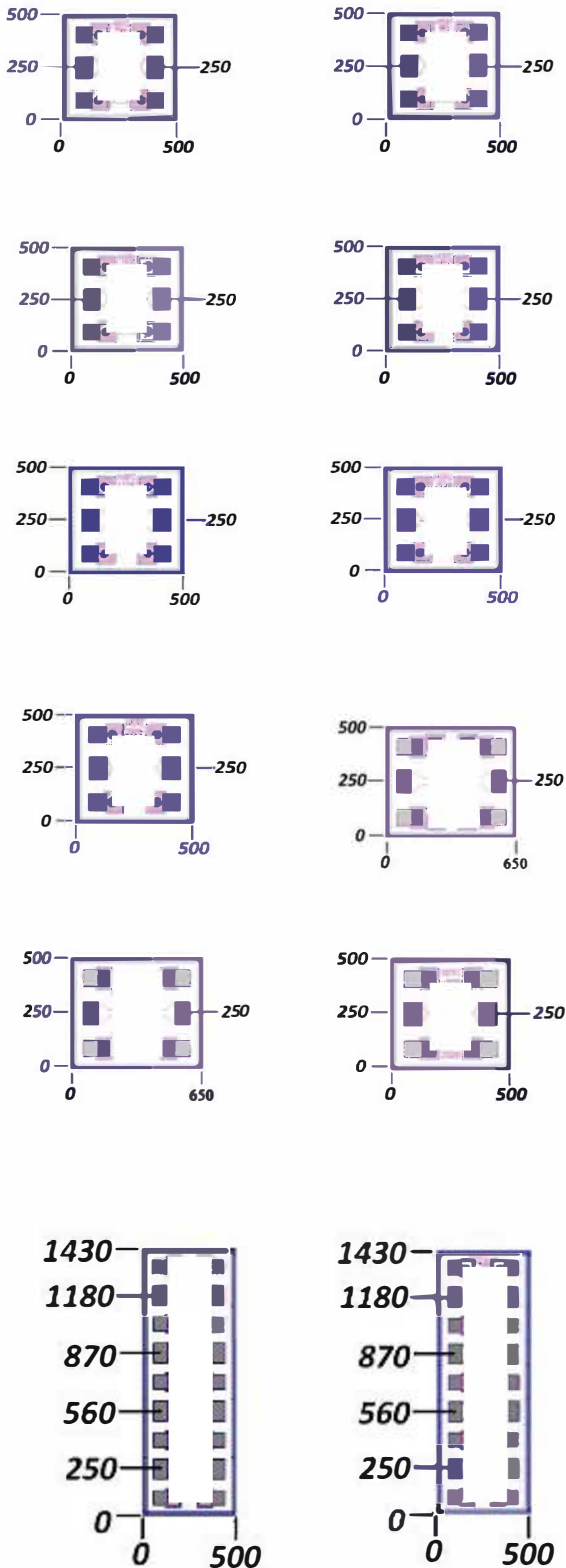
Note: The anti-static level is level 0 (200V).



The assembly drawings for other models are the same as above.

**Note:**

- 1) Assemble and use in a purified environment.
- 2) GaAs material is very brittle and the surface of the chip is easily damaged (do not touch the surface). When using automatic mounting, use a rubber suction head. When clamping the chip, avoid metal or other hard objects from contacting the chip surface and be careful when clamping.
- 3) Use 2 bonding wires (with a diameter of 25um gold wire) for input and output, and keep the bonding wires as short as possible, not longer than 500um.
- 4) Input and output without DC blocking capacitors.
- 5) Use 80/20 gold tin sintering, with a sintering temperature not exceeding 300 ° C and a sintering time as short as possible, not exceeding 30 seconds.
- 6) This product belongs to electrostatic sensitive devices. Please pay attention to anti-static measures during storage and use. The anti-static level is level 0 (200V).
- 7) Store in a dry and nitrogen environment.
- 8) Do not attempt to clean the surface of the chip using dry or wet chemical methods.
- 9) Please contact the supplier if you have any questions.



Note: All dimensions are in micrometers ( $\mu\text{m}$ ); RF pressure point size 80x110  $\mu\text{m}^2$ .